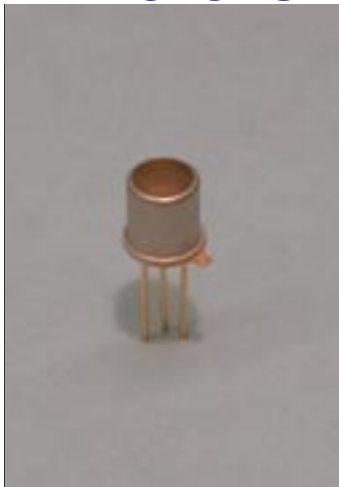
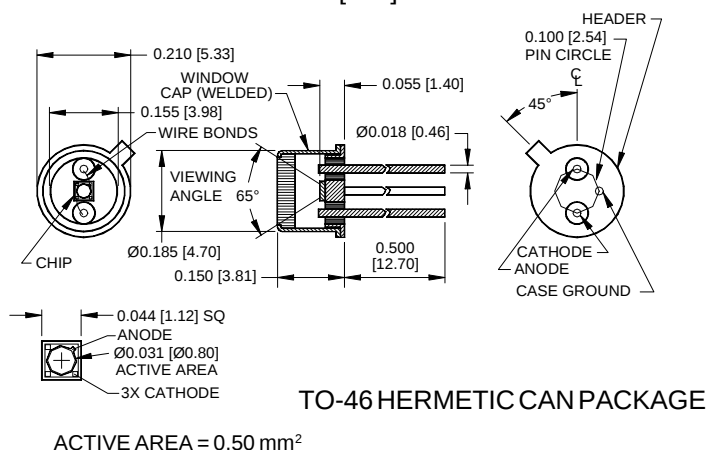


PHOTONIC DETECTORS INC. Gallium Nitride (GaN), Ultra Violet (U.V.) Schottky Photodiode Type PDU-G102



PACKAGE DIMENSIONS inch [mm]



FEATURES

- 0.194 A/W @ 360 nm
- High shunt resistance
- 360 nm peak response
- Short wavelength resp.

DESCRIPTION

The **PDU-G102** is a GaN, planar passivated U.V. photodiode. Spectral range from 200 nm to 350 nm with a 0.80 mm diameter (.50 mm²) active area. Packaged in a isolated TO-18 with U.V. transmitting window can.

APPLICATIONS

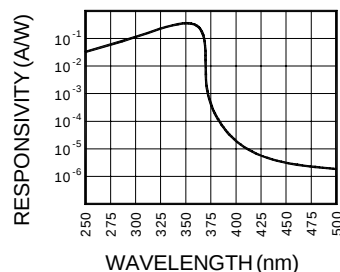
- Flame detectors
- U.V. sensors
- U.V. monitors
- U.V. instrumentation

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		100	V
T _{STG}	Storage Temperature	-55	+150	°C
T _O	Operating Temperature Range	-40	+125	°C
T _S	Soldering Temperature*		+240	°C
I _L	Light Current		0.5	mA

*1/16 inch from case for 3 secs max

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{SC}	Short Circuit Current	H = 100 fc, 360 nm	40	30		μA
I _D	Dark Current	H = 0, V _R = 10 mV		130	150	pA
R _{SH}	Shunt Resistance	H = 0, V _R = 10 mV	50	75		MΩ
TCR _{SH}	RSH Temp. Coefficient	H = 0, V _R = 10 mV		-8		% / °C
C _J	Junction Capacitance	H = 0, V _R = 10 V**		30	50	pF
λ range	Spectral Application Range	Spot Scan	200		425	nm
λ _p	Spectral Response - Peak	Spot Scan		360		nm
V _{BR}	Breakdown Voltage	I = 10 μA		3		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		1.5x10 ⁻¹⁴		W/√Hz
tr	Response Time	RL = 1 KΩ V _R = 3 V		1		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f = 1MHz